

## Cool MOS™ Power Transistor



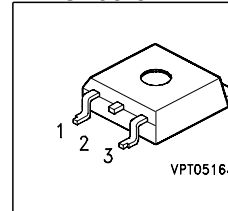
### Feature

- New revolutionary high voltage technology
- Worldwide best  $R_{DS(on)}$  in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- Ultra low effective capacitances
- Improved noise immunity

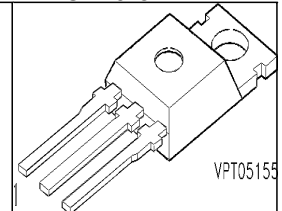
### Product Summary

$V_{DS}$	800	V
$R_{DS(on)}$	290	m $\Omega$
$I_D$	17	A

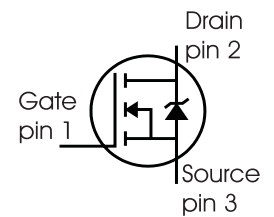
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP17N80C3	P-TO220-3-1	Q67040-S4353	17N80C3
SPB17N80C3	P-TO263-3-2	Q67040-S4354	17N80C3



### Maximum Ratings, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_D$	17 11	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\ puls}$	51	
Avalanche energy, single pulse $I_D=4A, V_{DD}=50V$	$E_{AS}$	670	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1)</sup> $I_D=17A, V_{DD}=50V$	$E_{AR}$	0.5	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	17	A
Reverse diode $dv/dt$ $I_S=17A, V_{DS} < V_{DD}, di/dt=100A/\mu s, T_{jmax}=150^\circ\text{C}$	$dv/dt$	6	V/ns
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation, $T_C = 25^\circ\text{C}$	$P_{tot}$	208	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	62	
		-	35	-	
Linear derating factor		-	-	1.67	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	°C

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

#### Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	800	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=17A$	$V_{(BR)DS}$	-	870	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=1mA$	$V_{GS(th)}$	2	3	4	
Zero gate voltage drain current $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, T_j = 150\text{ °C}$	$I_{DSS}$	-	0.5	25	μA
		-	-	250	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	$I_{GSS}$	-	-	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=11A, T_j=25\text{ °C}$	$R_{DS(on)}$	-	250	290	mΩ
Gate input resistance $f = 1\text{ MHz}, \text{open drain}$	$R_G$	-	0.7	-	Ω

<sup>1</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Characteristics</b>						
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 11\text{A}$	-	15	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ ,	-	2320	-	pF
Output capacitance	$C_{oss}$	$f = 1\text{MHz}$	-	1250	-	
Reverse transfer capacitance	$C_{rss}$		-	60	-	
Effective output capacitance, <sup>1)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 640\text{V}$	-	59	-	pF
Effective output capacitance, <sup>2)</sup> time related	$C_{o(tr)}$		-	124	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{V}$ , $V_{GS} = 0/10\text{V}$ ,	-	45	-	ns
Rise time	$t_r$	$I_D = 17\text{A}$ , $R_G = 5.6\Omega$ ,	-	17	-	
Turn-off delay time	$t_{d(off)}$	$T_j = 125^\circ\text{C}$	-	77	88	
Fall time	$t_f$		-	10	13	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	9	-	nC
Gate to drain charge	$Q_{gd}$		-	42	-	
Gate charge total	$Q_g$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	83	107	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	6	-	V

<sup>1</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>2</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

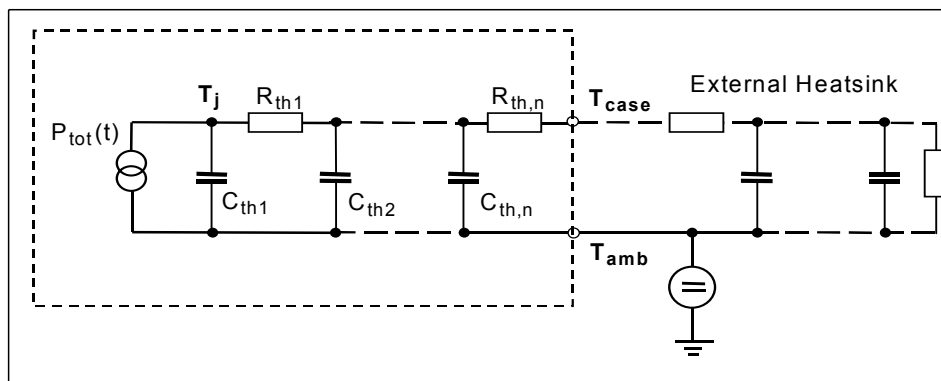
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Reverse Diode</b>						
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	17	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	51	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{V}, I_F=I_S,$	-	550	-	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	13	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	40	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	1200	-	$\text{A}/\mu\text{s}$

**Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	

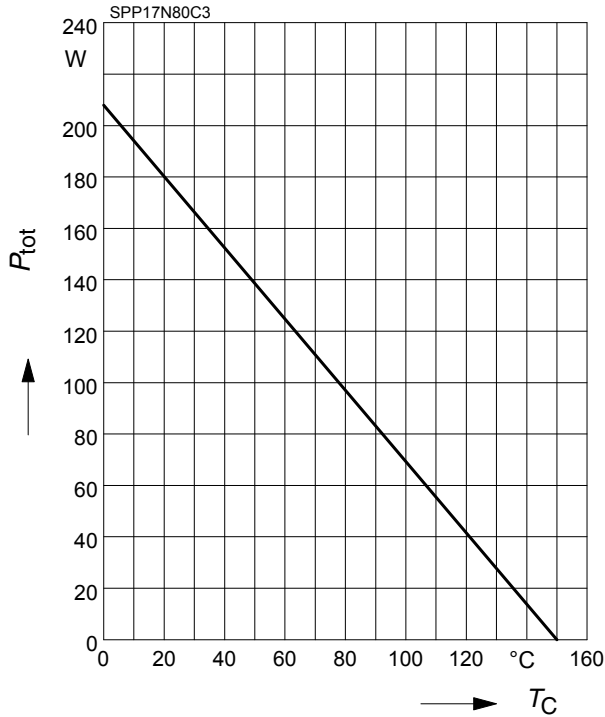
**Transient thermal impedance**

Thermal resistance			Thermal capacitance		
$R_{th1}$	0.00716	K/W	$C_{th1}$	0.000441	Ws/K
$R_{th2}$	0.01		$C_{th2}$	0.0014	
$R_{th3}$	0.022		$C_{th3}$	0.000985	
$R_{th4}$	0.065		$C_{th4}$	0.0045	
$R_{th5}$	0.083		$C_{th5}$	0.02	
$R_{th6}$	0.038		$C_{th6}$	0.146	



### 1 Power dissipation

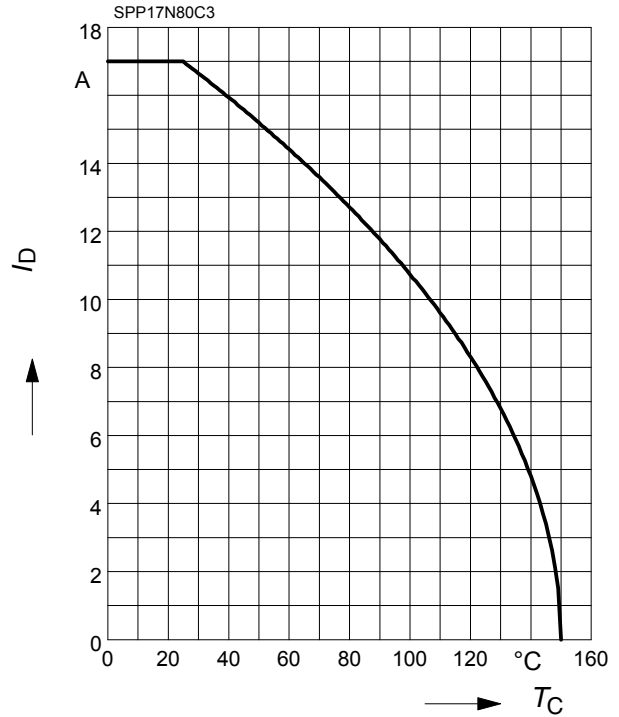
$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

$$I_D = f(T_C)$$

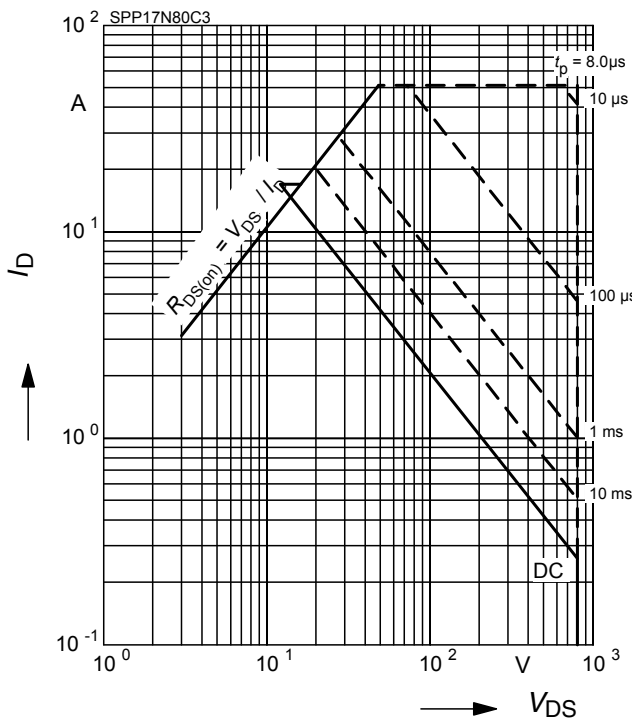
parameter:  $V_{GS} \geq 10 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

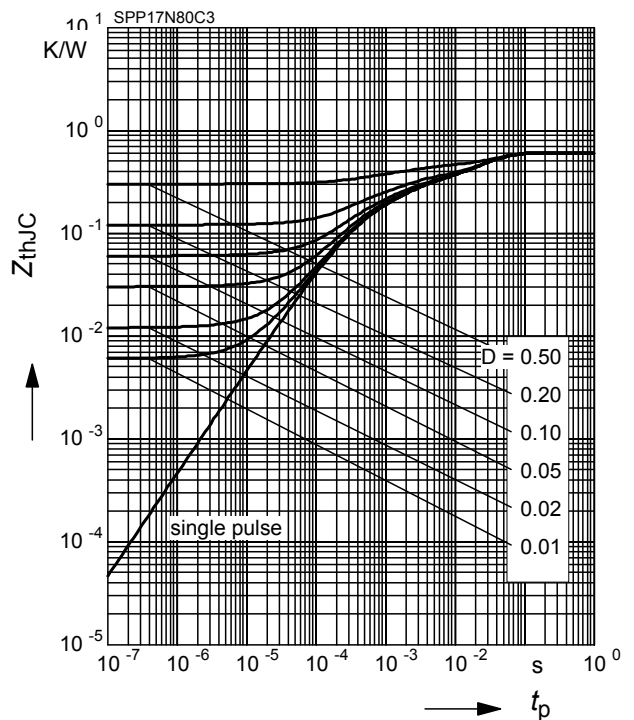
parameter:  $D = 0$ ,  $T_C = 25^\circ\text{C}$



### 4 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

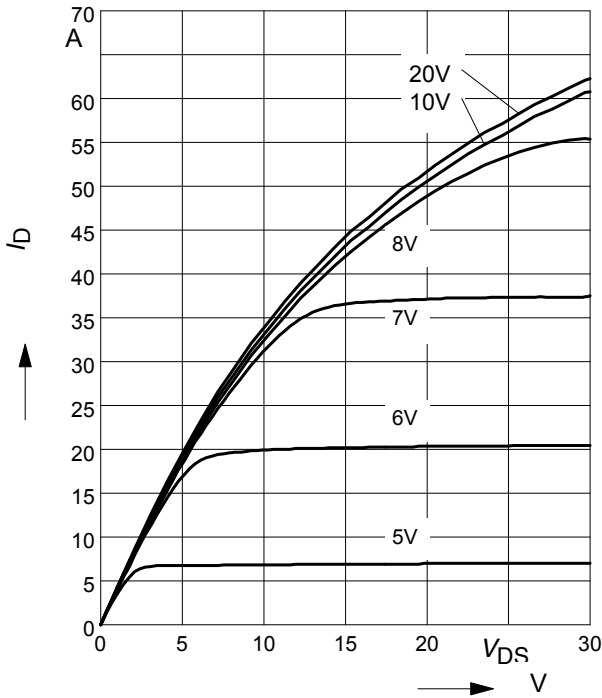
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

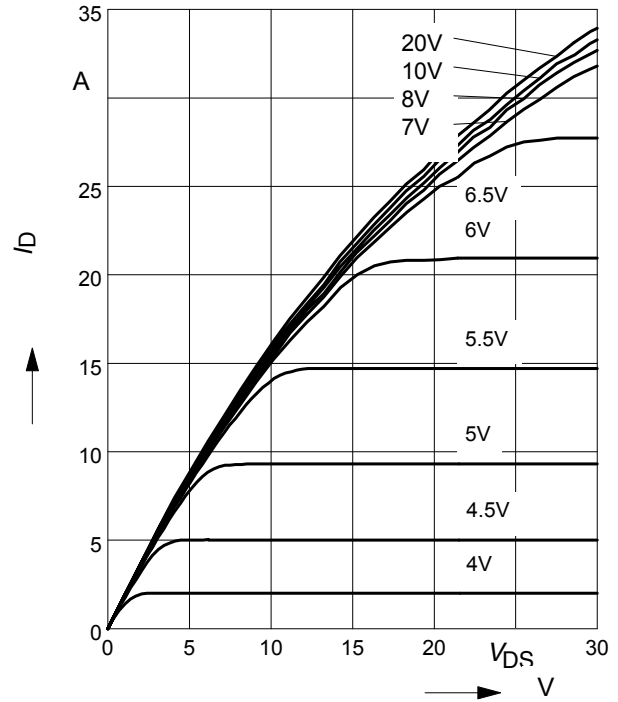
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**6 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

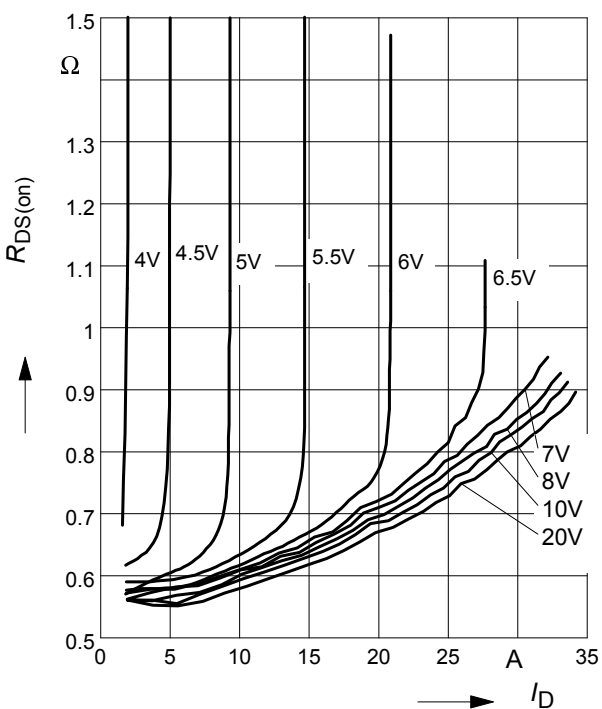
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**7 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

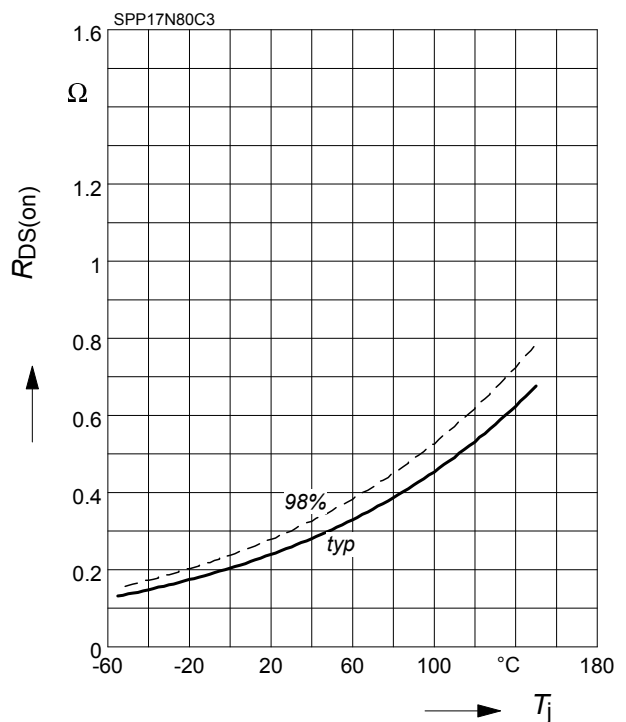
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



**8 Drain-source on-state resistance**

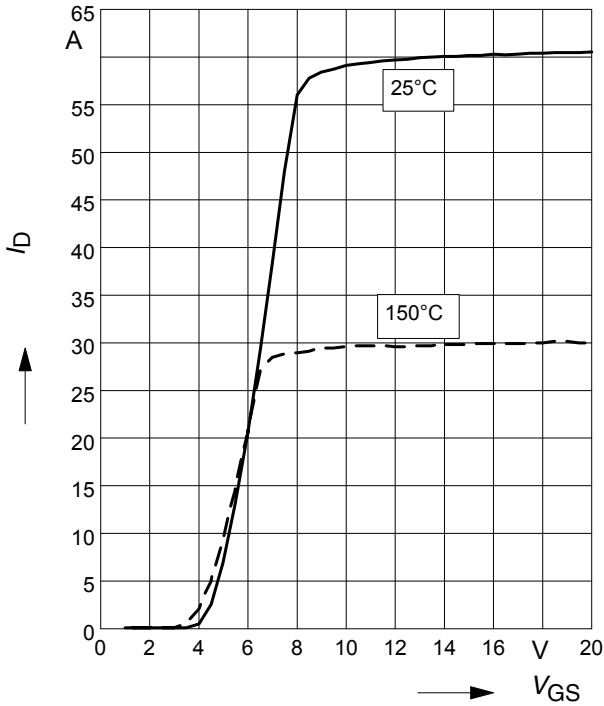
$R_{DS(on)} = f(T_j)$

parameter:  $I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}$



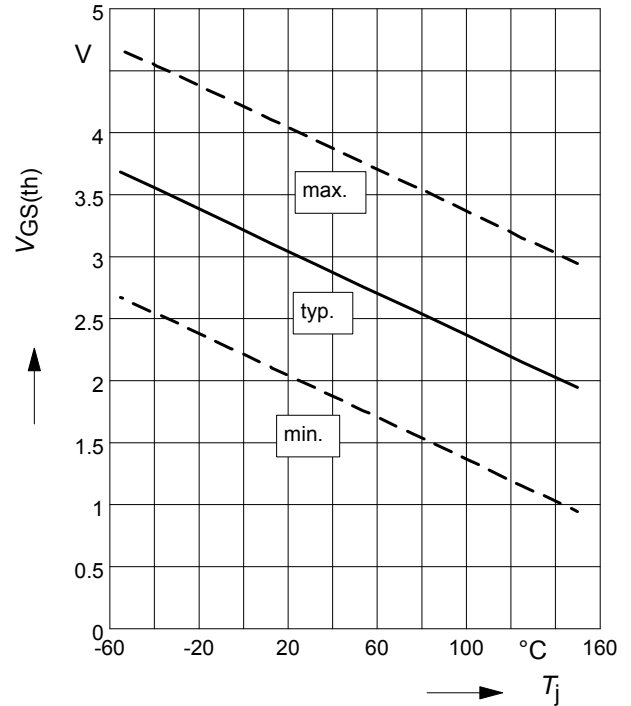
**9 Typ. transfer characteristics**

$I_D = f(V_{GS})$ ;  $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$   
parameter:  $t_p = 10 \mu s$



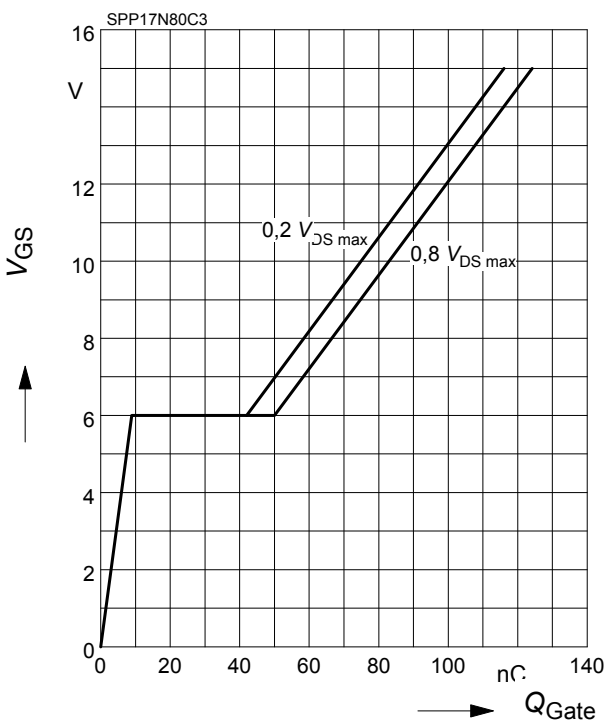
**10 Gate threshold voltage**

$V_{GS(th)} = f(T_j)$   
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = 1 mA$



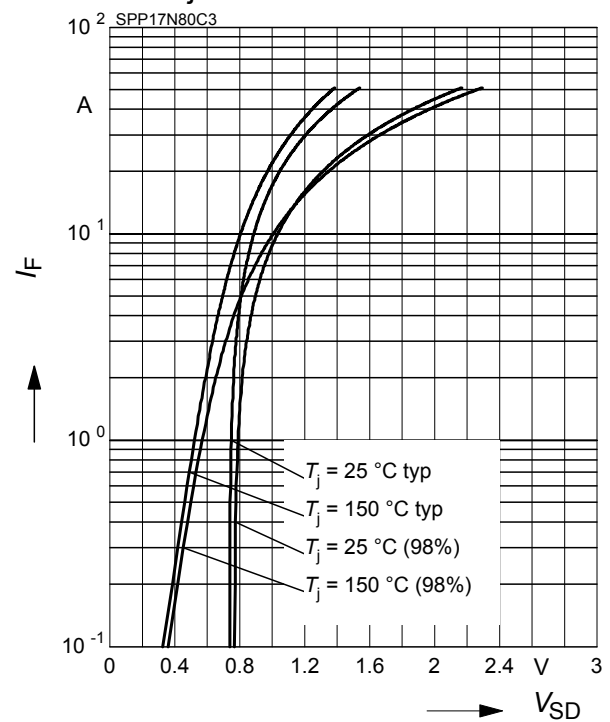
**11 Typ. gate charge**

$V_{GS} = f(Q_{Gate})$   
parameter:  $I_D = 17 A$  pulsed



**12 Forward characteristics of body diode**

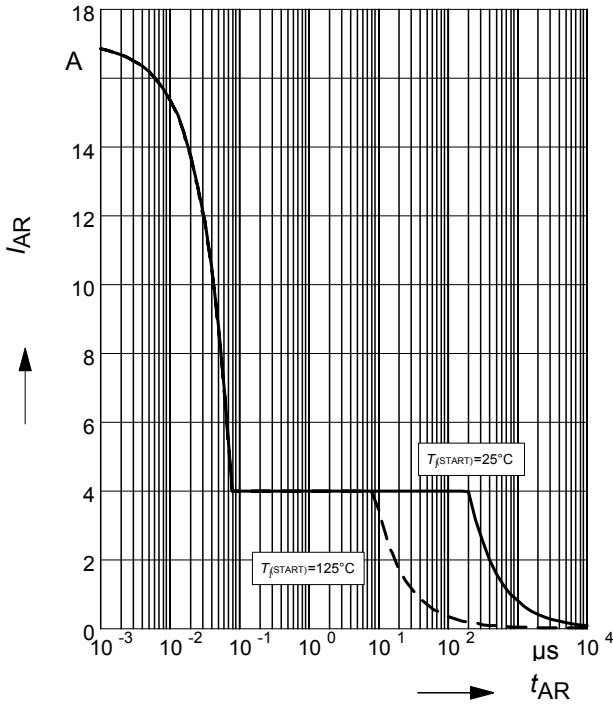
$I_F = f(V_{SD})$   
parameter:  $T_j$ ,  $t_p = 10 \mu s$



### 13 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

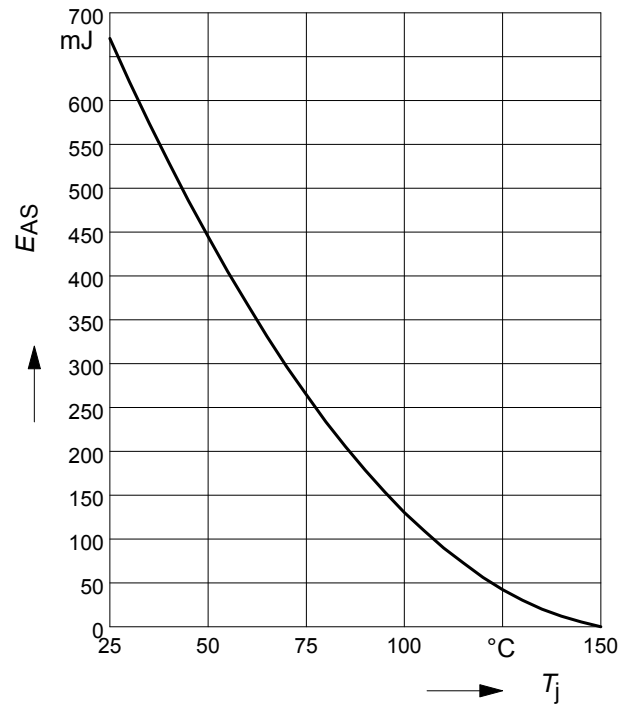
par.:  $T_j \leq 150\text{ }^\circ\text{C}$



### 14 Avalanche energy

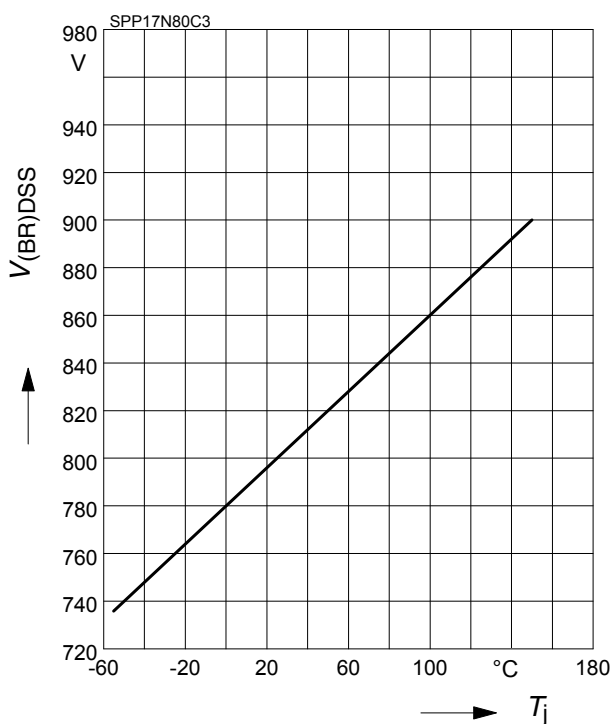
$$E_{AS} = f(T_j)$$

par.:  $I_D = 4\text{ A}$ ,  $V_{DD} = 50\text{ V}$



### 15 Drain-source breakdown voltage

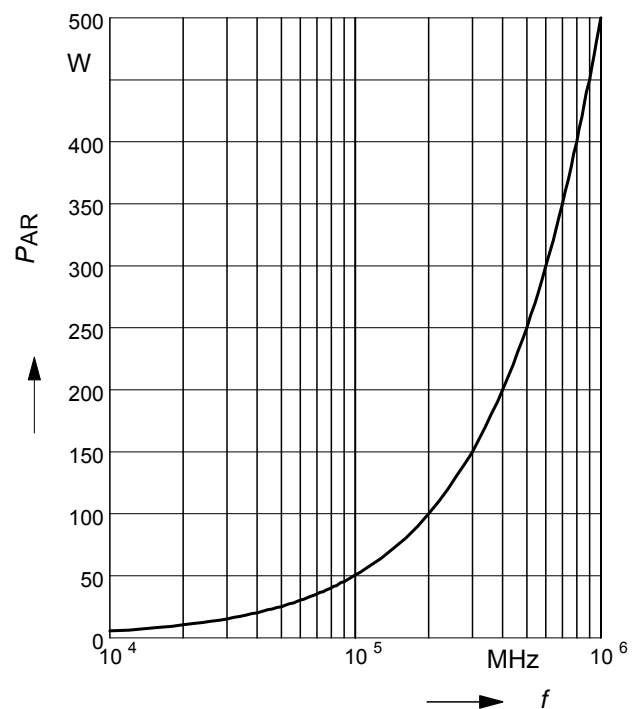
$$V_{(BR)DSS} = f(T_j)$$



### 16 Avalanche power losses

$$P_{AR} = f(f)$$

parameter:  $E_{AR} = 0.5\text{ mJ}$

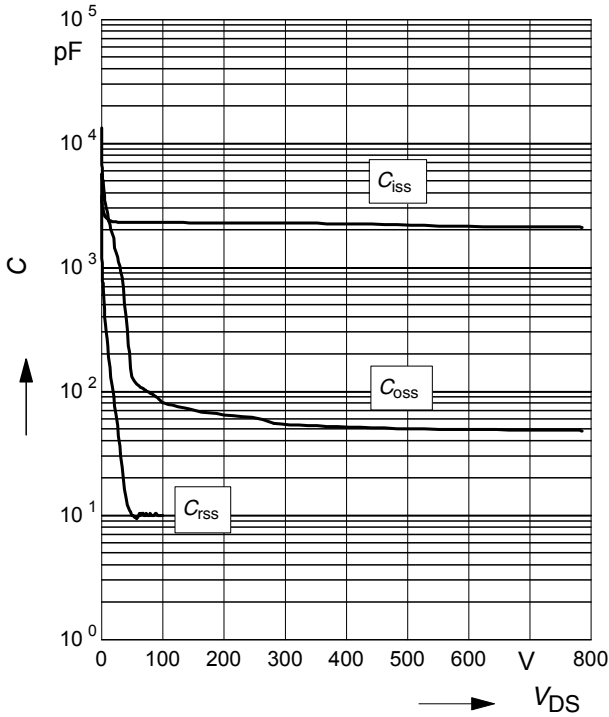




17 Typ. capacitances

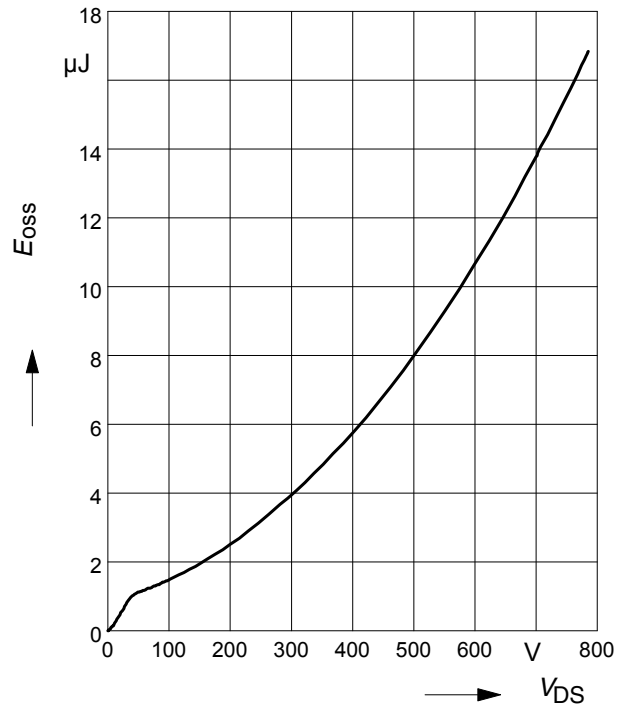
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0V, f=1\text{ MHz}$

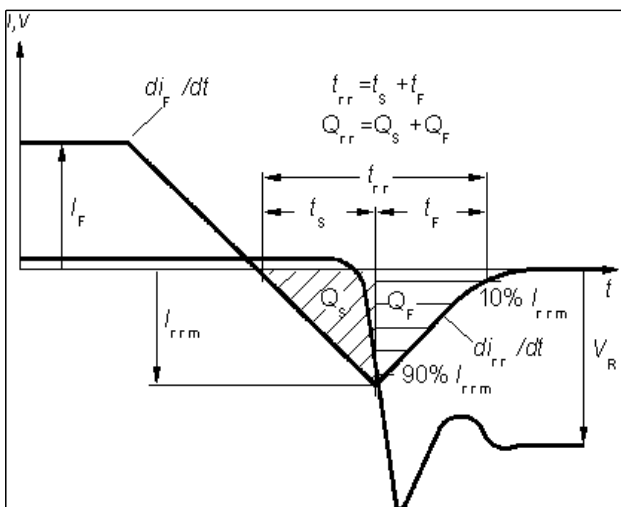


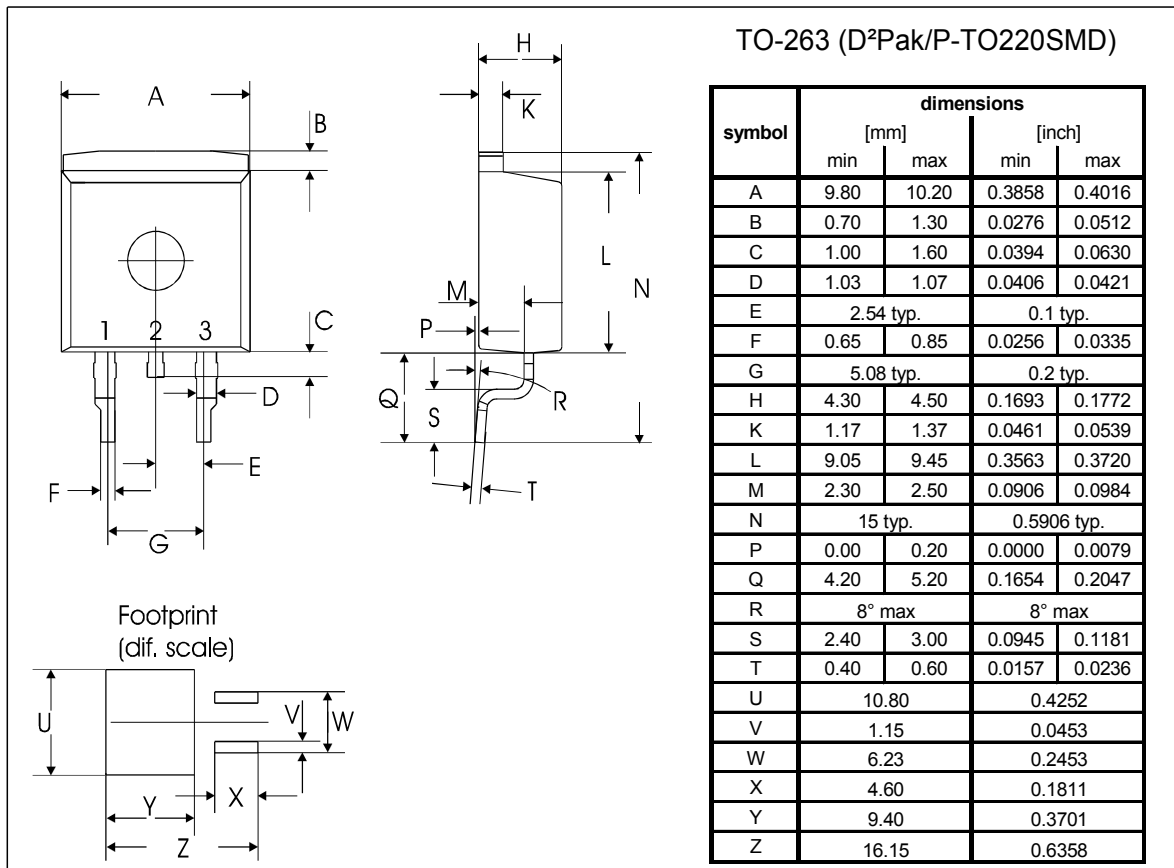
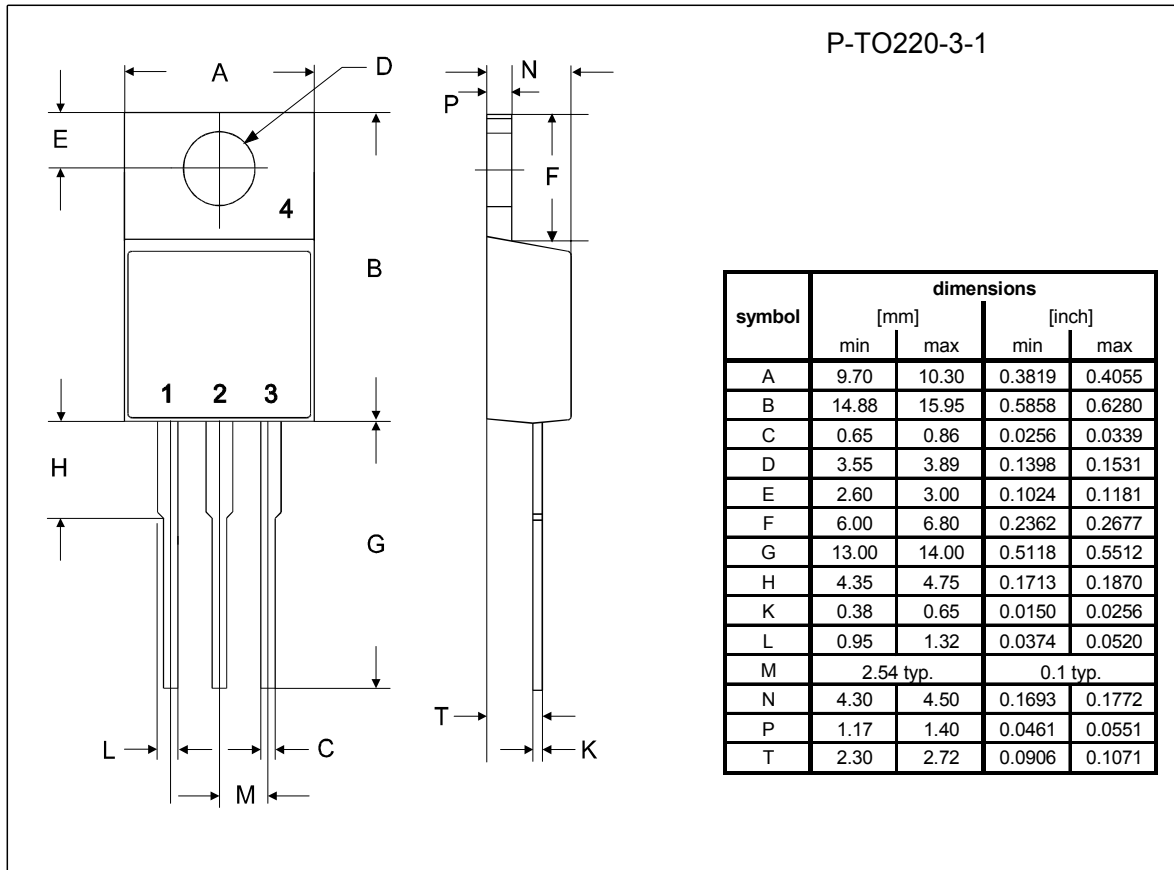
18 Typ.  $C_{oss}$  stored energy

$$E_{Oss} = f(V_{DS})$$



Definition of diodes switching characteristics





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